

PART 1 of 2

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PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Yuanning Chen, et al.

Serial No.: 09/597,076

Filed: January 20, 2000

For: PROCESS FOR FABRICATING OXIDES

Group No.: 2813

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Sir:

THIRD SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. §1.56, and in accordance with the provisions of 37 C.F.R. §§1.97 and 1.98 and §609 of the Manual of Patent Examining Procedure, Applicant hereby makes an additional disclosure of the patents, publications and other information listed below and on the accompanying form PTO-1449, which references are considered to be potentially material to the patentability of the invention disclosed in the above-referenced application. Copies of the listed references are submitted herewith. Disclosure has been filed previously on April 30, 2001, August 29, 2001 and August 5, 2002.

11/08/2002 CCHAU1 00000088 09597076

01 FC:1806 180.00 DP

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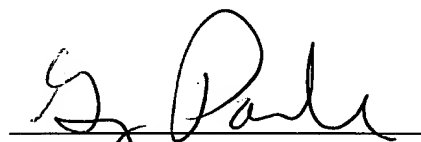
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Applicant hereby expressly reserves the right to swear behind the effective dates of any of the above patents and to question the relevance and materiality of the patents listed herein, in whole, in part or in combination, subsequent to filing this Information Disclosure Statement.

A check in the amount of \$ 180.00 is enclosed in payment of the filing fee for this communication. However, the Commissioner is hereby authorized to charge any additional fees connected with this communication or credit any overpayment to Deposit Account No. 08-2395.

Respectfully submitted,

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